

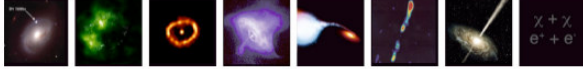
Desarrollo de detectores de CdTe para aplicaciones espaciales en el ICE-CSIC

Margarita Hernanz

Instituto de Ciencias del Espacio (CSIC-IEEC)

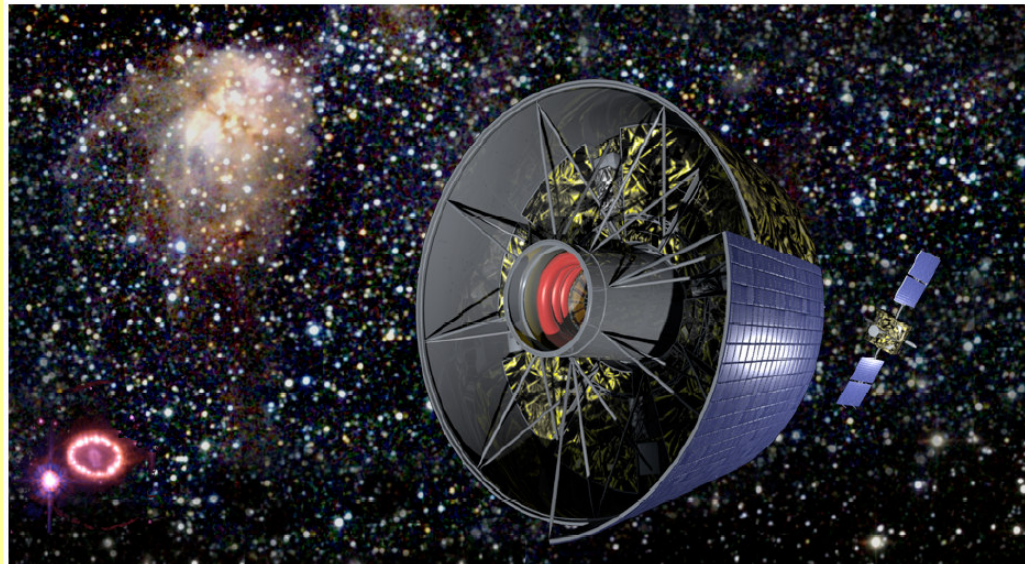
Doble interés en XEUS: científico y tecnológico

- Antecedentes **científicos**:
 - Explosiones estelares (novas y supernovas): modelos, nucleosíntesis y emisión a altas energías (X y γ)
 - Usuarios asiduos de XMM-Newton
 - Propuestas ToO para INTEGRAL
 - Participación en el equipo científico de la propuesta de NASA ACT (y GRASP)
- **Instrumentación** para astrofísica de altas energías
 - Prototipo de lente de focalización de rayos γ CLAIRE (colaboración CESR, Toulouse)
 - Participación en la propuesta de misión Gamma-Ray Imager (GRI), Cosmic Vision 2015-2025



GRI

exploring the extremes



Jürgen Knödseder, Peter von Ballmoos (CESR, France)
 Filippo Frontera (UNIFE, Italy), Angela Bazzano (INAF/IASF-Rome, Italy)
 Finn Christensen (DNSS, Denmark)
 Margarida Hernanz (IEEC/CSIC, Spain)
 Cornelia B. Wunderer (UCB, USA)

This proposal has been prepared by the GRI consortium, formed by about 100 scientists from the following countries (in alphabetical order): Belgium, China, Denmark, France, Germany, Ireland, Italy, Poland, Portugal, Russia, The Netherlands, Spain, Turkey, United Kingdom, and USA
 A complete list of consortium members can be found at <http://gri.iasf-roma.inaf.it/GRI/MemberList.asp>



Proyecto R&D PNE (2008)

Diseño, desarrollo y test de un
prototipo de cámara Compton
Si/CdTe

Si y CdTe apilado – ref. Takahashi

*Colaboración con
IMB/CNM (CSIC)*

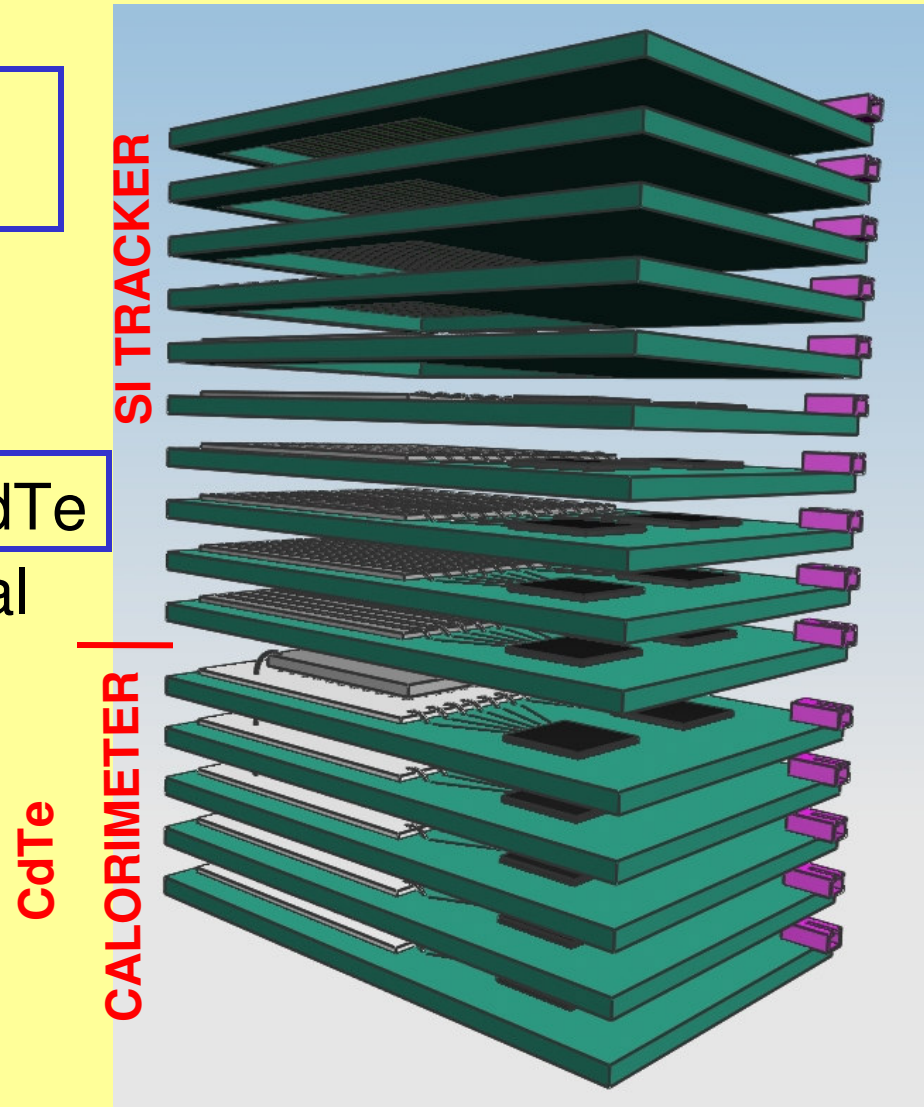
***OBJETIVO: contribuir al
estudio conceptual del
detector de GRI***

Optimizar el diseño mediante simulaciones
con GEANT4.

Reto: detectar γ 's con E hasta 1(-2) MeV con
resolución energética óptima

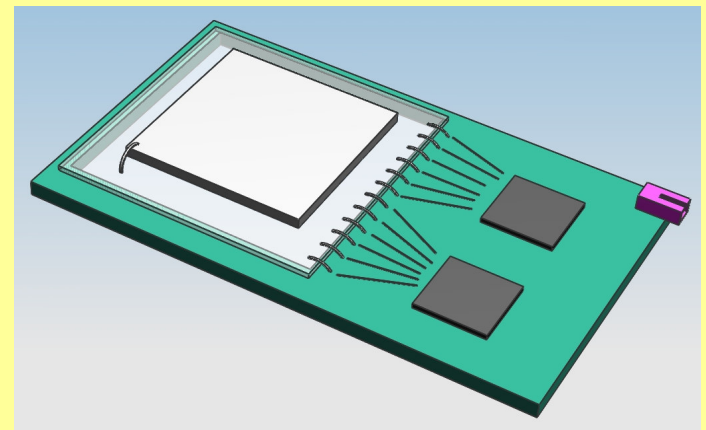
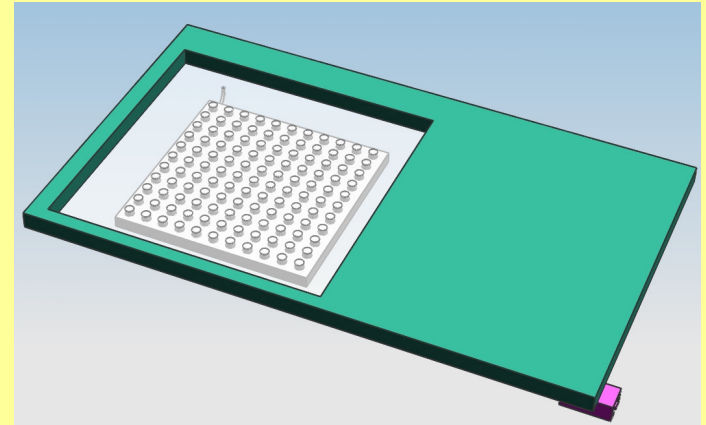
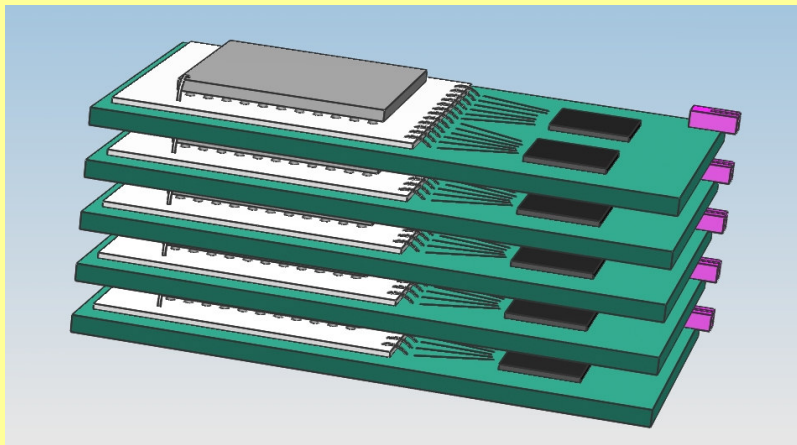
Compton camera

- Tracker/moderator: Si
- Calorimeter/absorber: stacked CdTe
- Read out electronics
 - Make use of adapted LHC electronics for Si detectors
 - NuCam chip from RAL for CdTe
- Readout DAQ based on National Instruments and LabView
- GEANT4 simulations:
 - optimization of the design
 - comparison of simulations with measurements
 - simulations in space environment



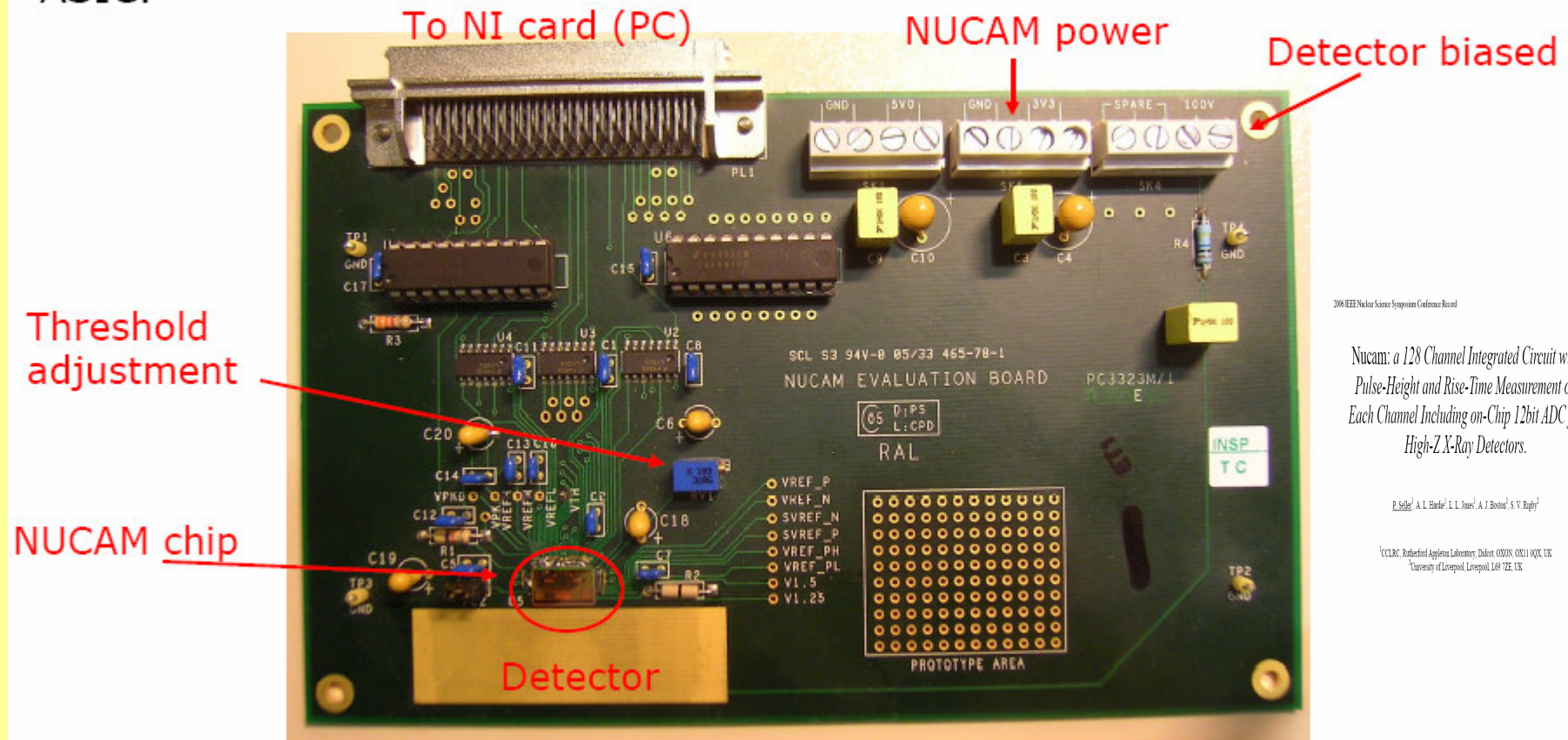
Compton camera: CdTe calorimeter

- Pixellated CdTe: $11 \times 11 = 121$ pixels
pixel size ~ 1 mm
- 5 layers
 - thickness 0.5, 1.0, 2.0, 4.0, and 8.0 mm
 - goal: good energy resolution for gamma rays in the range 150 keV to 1-2 MeV



NUCAM ASICs on Labview system

A Labview based test system has been built including an interface card for ASIC.



2006 IEEE Nuclear Science Symposium Conference Record

RIS4

Nucam: a 128 Channel Integrated Circuit with Pulse-Height and Rise-Time Measurement on Each Channel Including on-Chip 12bit ADC for High-Z X-Ray Detectors.

P. Sefel¹, A. L. Hinde¹, L. L. Jones¹, A. J. Bonnet², S. V. Bagby²

¹CLRC, Rutherford Appleton Laboratory, Didcot, OX11 0QX, UK
²University of Liverpool, Liverpool, L69 7ZE, UK

It allows us to control the ASIC and input calibration signals as well as to display raw data and perform simple statistical analysis of the values readout.

RAL/ICE/IMB collaboration

José Luis Gálvez ICE

Compton camera

- Moderator: Silicon
 - Double side 128 strips with a pitch of $200\ \mu\text{m}$
 - 10 layers

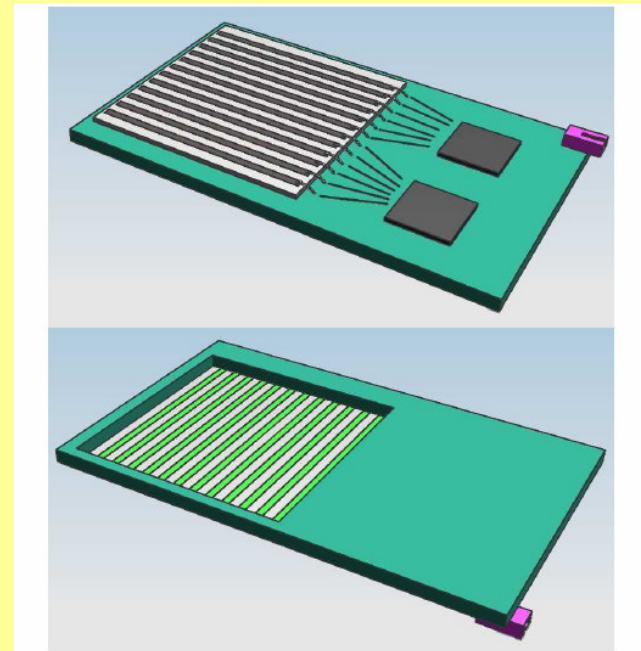
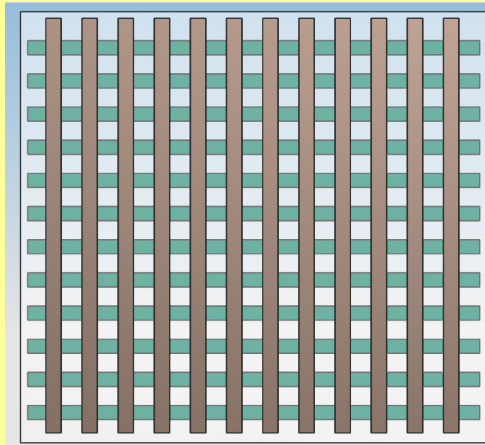
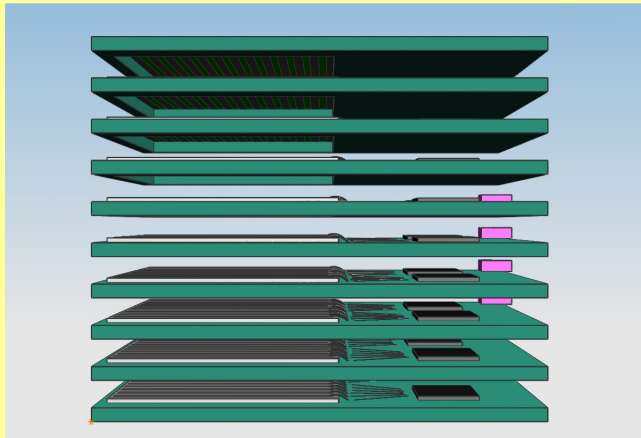
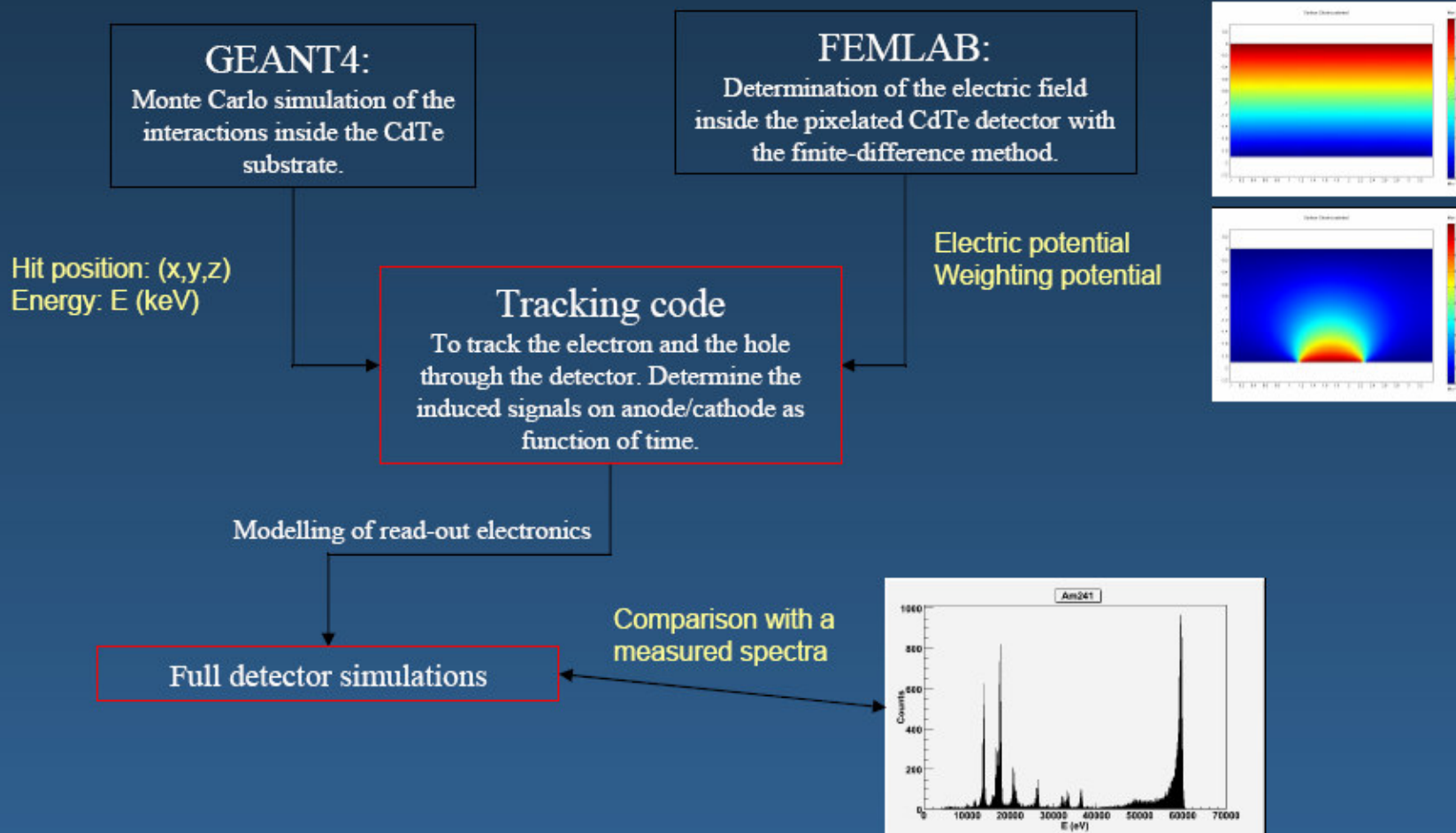


Figure 3. Top and bottom side of silicon modules

Geant4 SIMULATIONS

Simulation with Geant4

Modelling of pixelated CdTe detectors

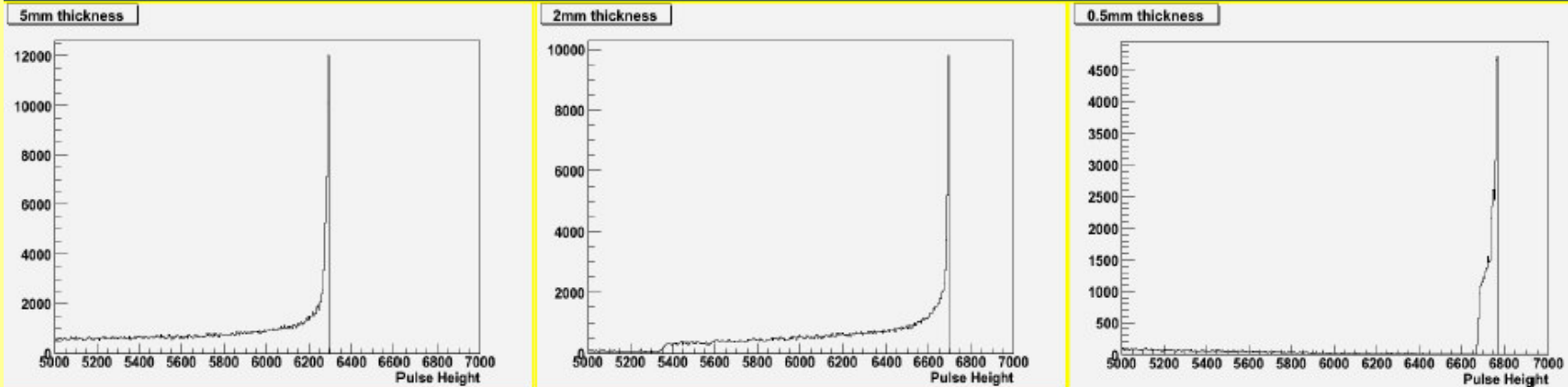


José M. Alvarez, ICE

Jornada XEUS, IFCA, Santander, 22 Febrero 2008

M. Hernanz

Pulse height spectra: tailing effect



Pulse Height spectra for various thicknesses of CdTe (5mm,2mm, and 0,5mm).

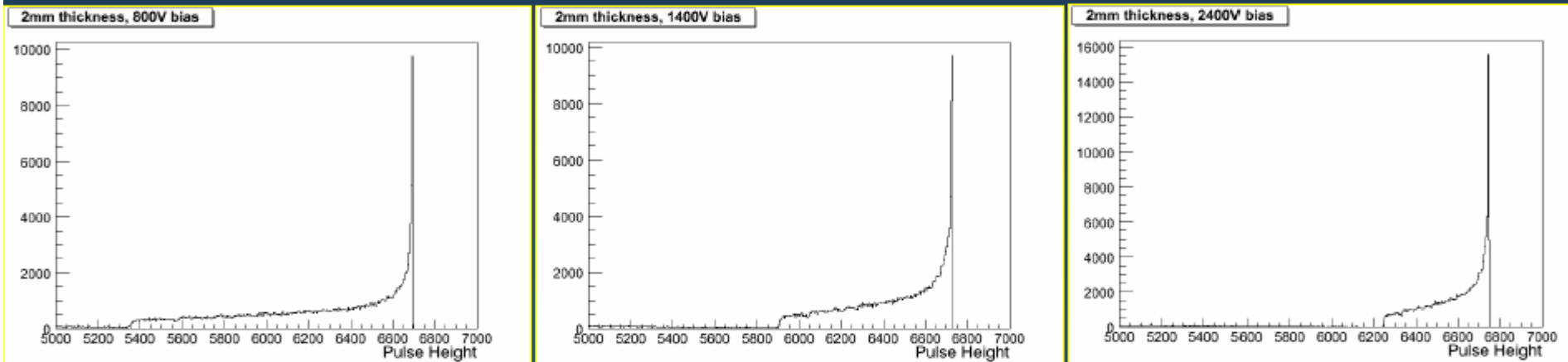
Hecht equation:
$$PH(z) \propto n_0 \left[\lambda_e \left(1 - \exp\left(-\frac{d-z}{\lambda_e}\right) \right) + \lambda_h \left(1 - \exp\left(-\frac{z}{\lambda_h}\right) \right) \right]$$

Uniform electric field: $E = V/d$ $\lambda_e = \mu_e \tau_e E$, $\lambda_h = \mu_h \tau_h E$

The number of photons injected 10^6 for each simulation with an energy of 300keV. The applied bias voltage is 800V, and we assumed an uniform electric field.

José M. Alvarez, ICE

Pulse height spectra: tailing effect



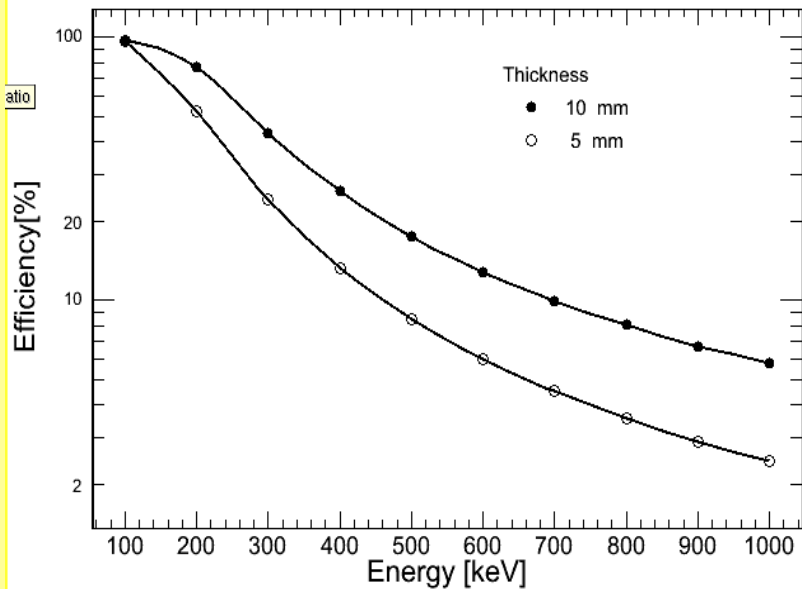
Pulse Height spectra for CdTe detector of 2 mm thickness for various applied bias voltage (800V, 1400V and 2400V).

For a certain detector thickness (2mm) the charge collection efficiency improves as the applied bias voltage increase.

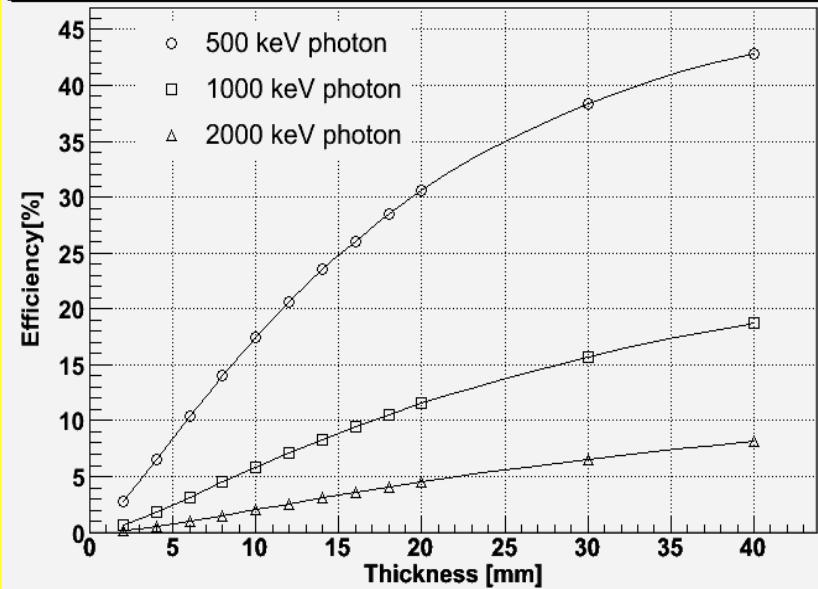
José M. Alvarez, ICE

Photo peak detection efficiency: monolithic CdTe detector

CdTe-Photo peak detection efficiency at different energies



CdTe - Photo peak detection efficiency at different thickness for various energies



CdTe & Ge- Photo peak detection efficiency for 0.5MeV photon at different thickness

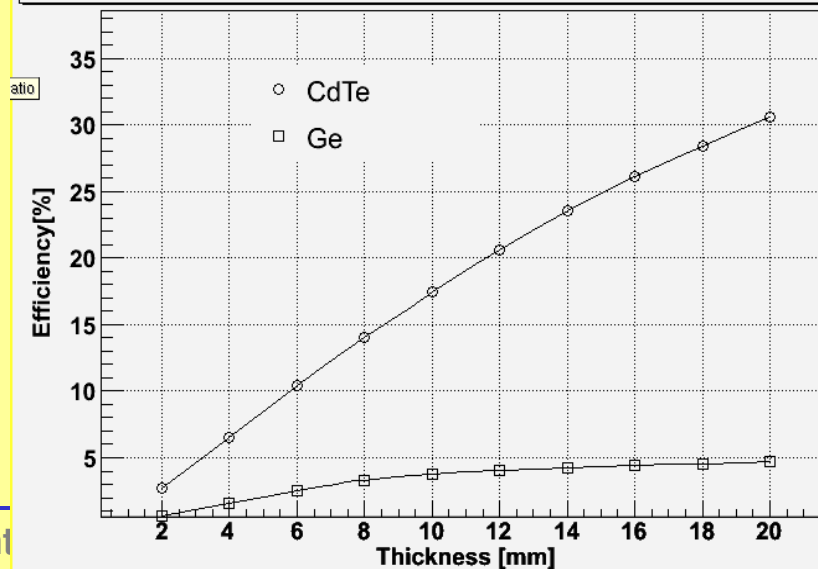
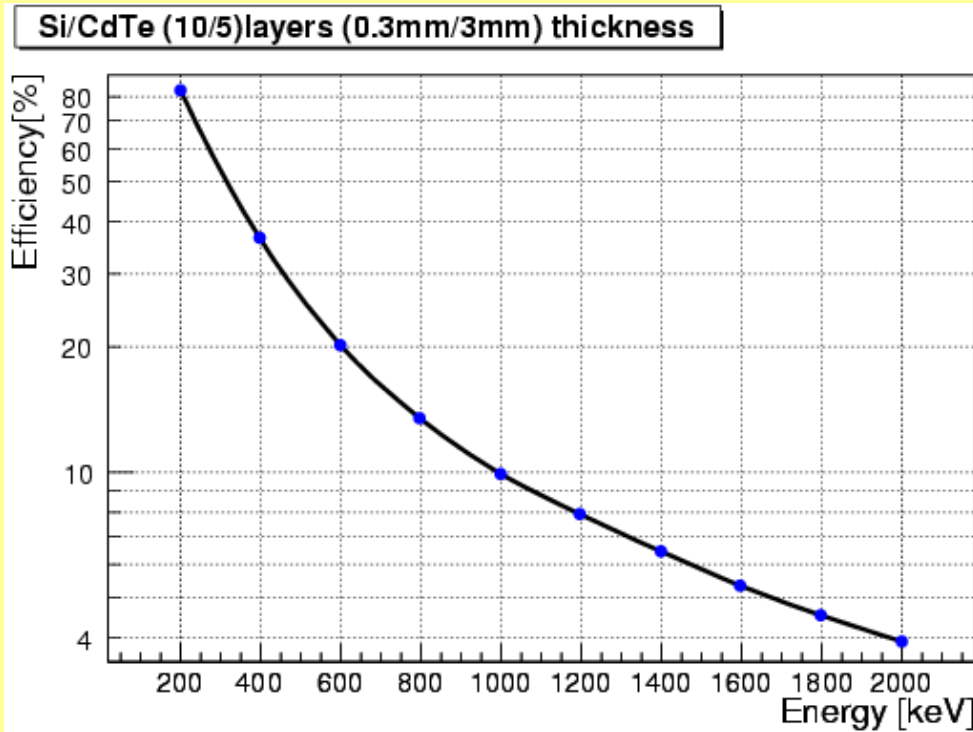
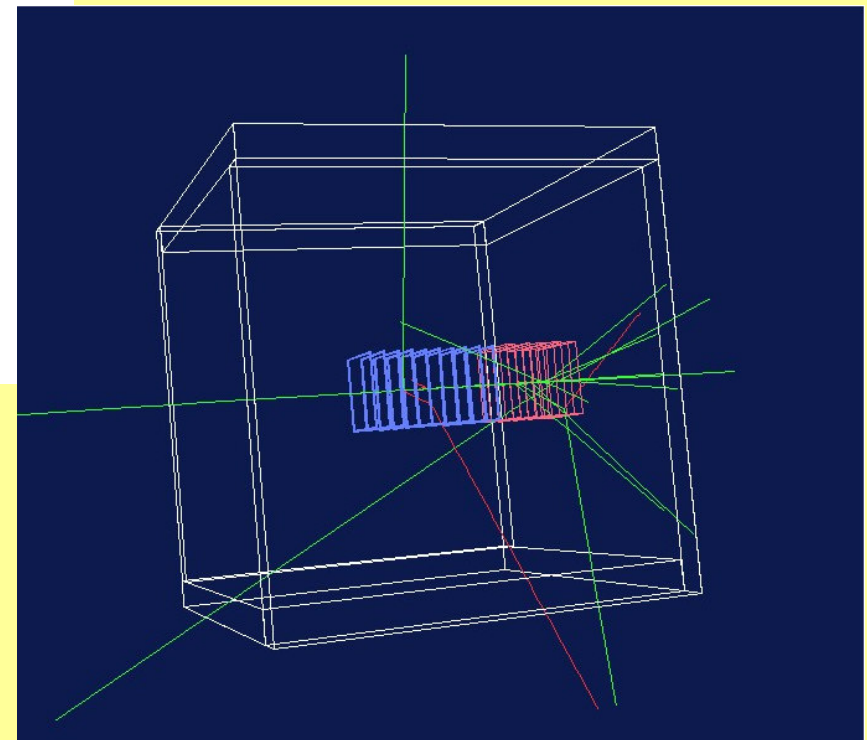


Photo peak detection efficiency: Si/CdTe stacked detector



Geant4 Geometry
10 layers of Si + 5 layers of CdTe



Ongoing and near future simulations

- Optimize readout electronics to improve the energy resolution
 - electric field inside the CdTe pixellated detector, to track the electrons and holes: *the 3D electric field will be calculated with a finite-difference method (FEMLAB)*
- *Event reconstruction: Compton sequence reconstruction with/without electron tracking (MEGAlib)*
- *Simulation of orbital background environment (MGGPOD)*